

**Electronic Supplementary Information for:**

**Scalable colloidal synthesis of  $\text{Bi}_{2.7}\text{Se}_{0.3}$  plate-like particles give access to high-performing n-type thermoelectric material for low temperature application**

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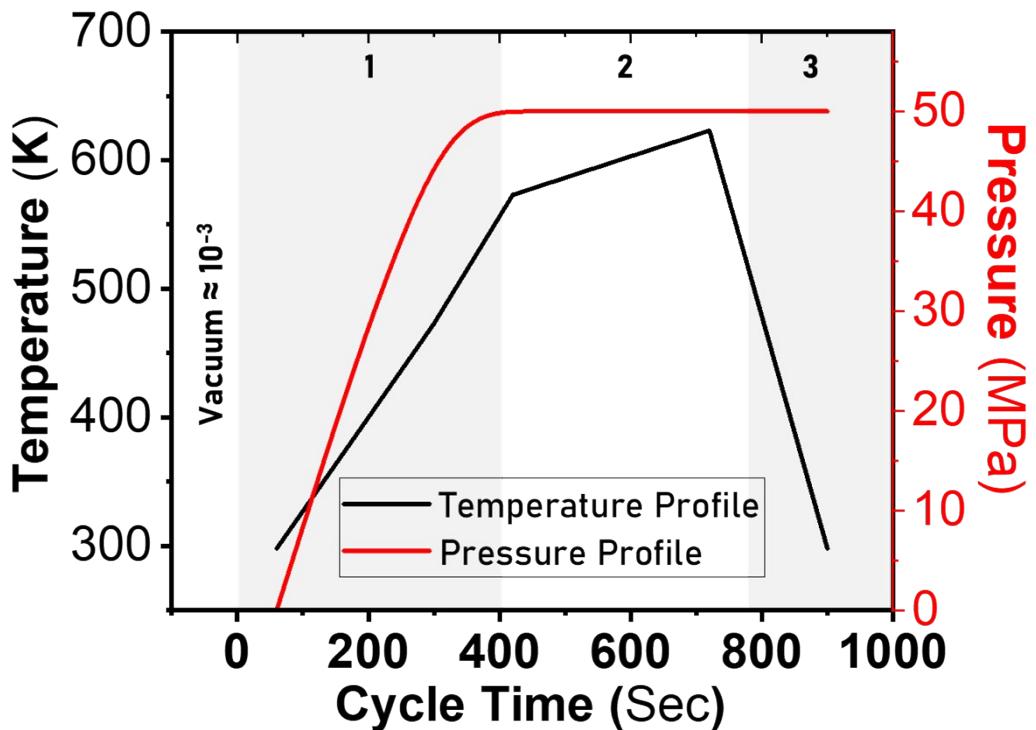
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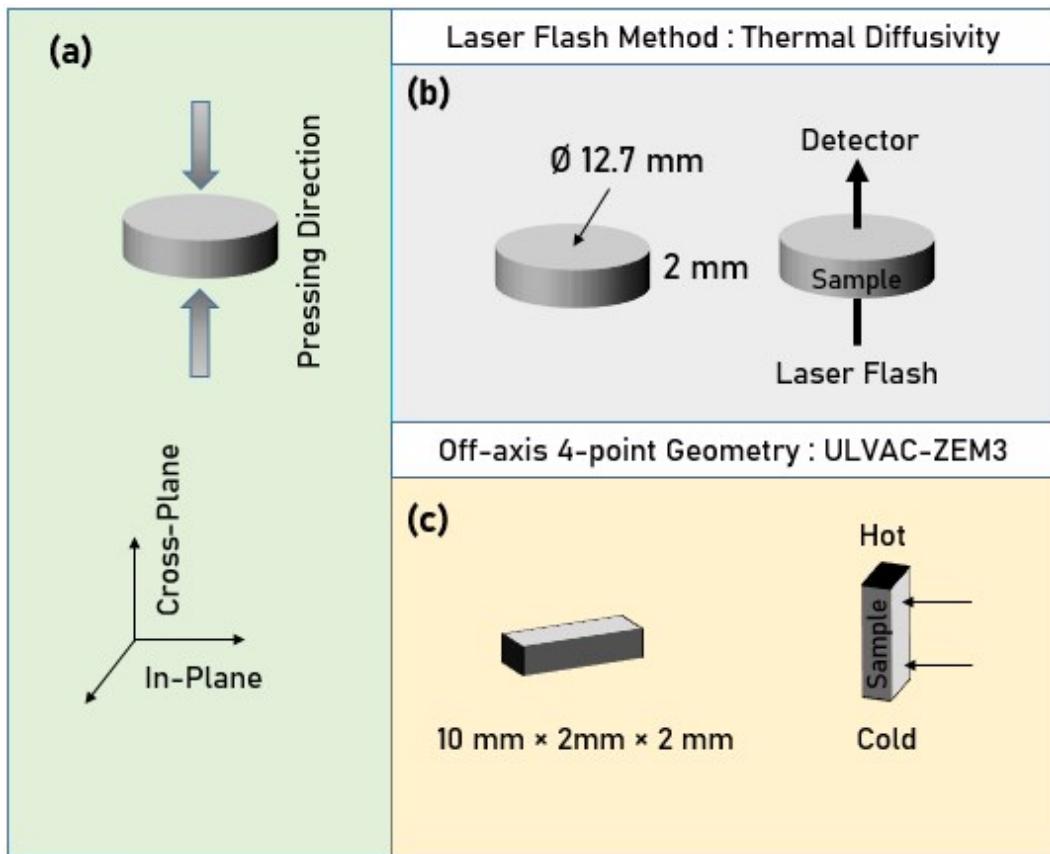
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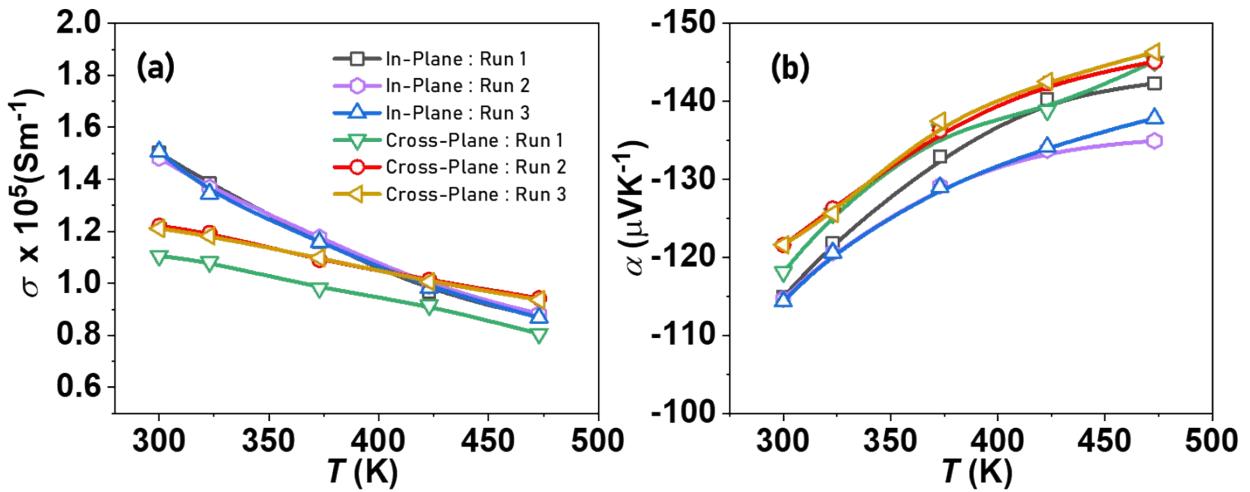
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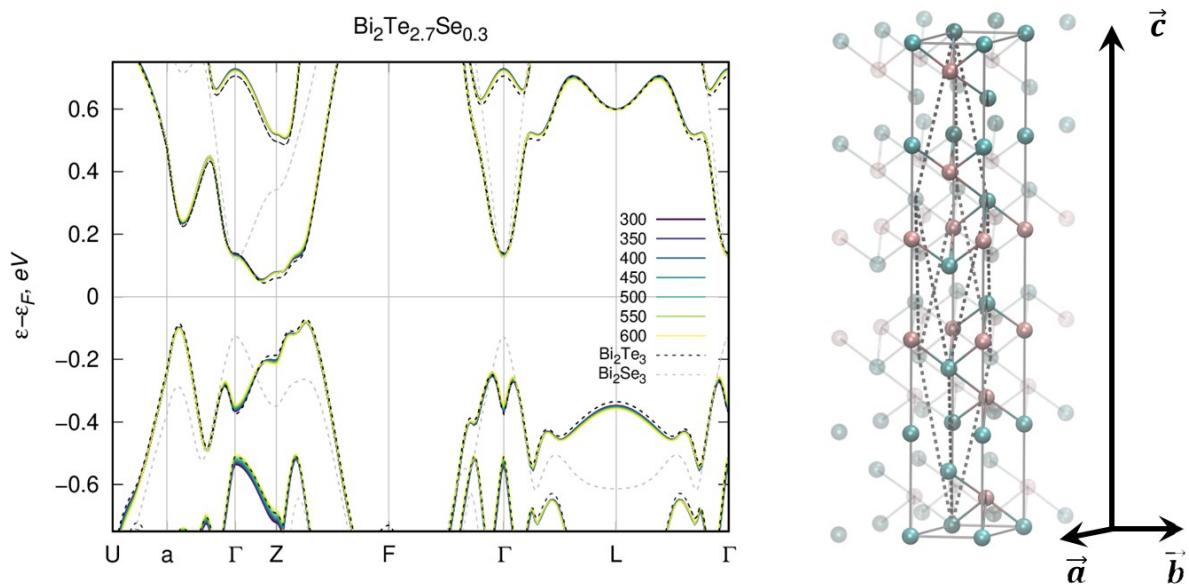
**Fig. S1.** Sintering profile for spark plasma sintered  $\text{Bi}_{2.7}\text{Se}_{0.3}$ .



**Fig. S2.** Schematic representation of direction and geometry for measurement of (a) thermal, and (b) electrical characterisation.



**Fig. S3:** Repeated measurement of temperature dependent electrical transport for synthesized  $\text{Bi}_2\text{Te}_{2.7}\text{Se}_{0.3}$  alloys (a) electrical conductivity, and (b) Seebeck coefficient.



**Fig. S4.** Left: doping and temperature effect on band structure. Special points correspond to the first Brillouin zone of rhombohedral lattice.<sup>1,2</sup> Right: correspondence between conventional hexagonal (solid lines) and primitive rhombohedral lattice (dashed lines).

## References:

1. Setyawan, W.; Curtarolo, S., High-throughput electronic band structure calculations: Challenges and tools. *Computational materials science* **2010**, 49, (2), 299-312.
2. Witting, I. T.; Chasapis, T. C.; Ricci, F.; Peters, M.; Heinz, N. A.; Hautier, G.; Snyder, G. J., The thermoelectric properties of bismuth telluride. *Advanced Electronic Materials* **2019**, 5, (6), 1800904.